



Title of Change:	Final PCN for wafer fab transfer from Gifu in Japan to Niigata in Japan (Group HU).																																																
Proposed first ship date:	19 September 2015																																																
Contact information:	Contact your local ON Semiconductor Sales Office or <Yasuhiro.Igarashi@onsemi.com>																																																
Samples:	Contact your local ON Semiconductor Sales Office																																																
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or <Kazutoshi.Kitazume@onsemi.com>.																																																
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <PCN.Support@onsemi.com>.																																																
Change Part Identification:	Affected products will be identified with date code.																																																
Change category(s): <input checked="" type="checkbox"/> Wafer Fab Change <input checked="" type="checkbox"/> Manufacturing Site Change/Addition <input type="checkbox"/> Product specific change <input type="checkbox"/> Assembly Change <input type="checkbox"/> Manufacturing Process Change <input type="checkbox"/> Datasheet/Product Doc change <input type="checkbox"/> Test Change <input type="checkbox"/> Material Change <input type="checkbox"/> Shipping/Packaging/Marking <input type="checkbox"/> Other: _____																																																	
Sites Affected: <input type="checkbox"/> All site(s) <input type="checkbox"/> not applicable <input checked="" type="checkbox"/> ON Semiconductor site(s) : <input type="checkbox"/> External Foundry/Subcon site(s):		Site 1 ON Niigata, Japan		Site 2 ON Gifu, Japan																																													
Description and Purpose: This is a Final Process Change Notification to announce the transfer of products from ON Semiconductor wafer fabrication sites located in Gifu Japan to the wafer fabrication ON Semiconductor Niigata Co., Ltd. (OSNC). OSNC is located in Niigata, Japan, obtained ISO9001 certification. The product design and electrical specifications will remain identical. A full electrical characterization over the temperature range will be performed for each product to check the device functionality and electrical specifications. Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards.																																																	
Reliability Data Summary: <table border="1"> <thead> <tr> <th>Test:</th> <th>Conditions:</th> <th>Interval:</th> <th>Results:</th> <th>Quantity:</th> </tr> </thead> <tbody> <tr> <td>Steady State Operating Life</td> <td>Tj=150degC</td> <td>1000 hrs</td> <td>Pass</td> <td>0/22</td> </tr> <tr> <td>High Temperature Reverse Bias</td> <td>Ta=150degC, VDSS =max</td> <td>1000 hrs</td> <td>Pass</td> <td>0/22</td> </tr> <tr> <td>Temp Humidity Storage</td> <td>Ta=85degC, RH=85%</td> <td>1000 hrs</td> <td>Pass</td> <td>0/22</td> </tr> <tr> <td>Temperature Cycle</td> <td>Ta=-55degC to 150degC 30min each</td> <td>100 cycles</td> <td>Pass</td> <td>0/22</td> </tr> <tr> <td>Pressure Cooker</td> <td>Ta=121degC, 2.03x105Pa, 100%</td> <td>50 hrs</td> <td>Pass</td> <td>0/22</td> </tr> <tr> <td>High Temperature Storage</td> <td>Ta=150degC</td> <td>1000 hrs</td> <td>Pass</td> <td>0/22</td> </tr> <tr> <td>Resistance to Soldering heat(Reflow)</td> <td>Solder Temp.: 260degC±5degC</td> <td>10 s</td> <td>Pass</td> <td>0/22</td> </tr> <tr> <td>Solderability</td> <td>Solder Temp.: 245degC±5degC</td> <td>5 s</td> <td>Pass</td> <td>0/22</td> </tr> </tbody> </table>					Test:	Conditions:	Interval:	Results:	Quantity:	Steady State Operating Life	Tj=150degC	1000 hrs	Pass	0/22	High Temperature Reverse Bias	Ta=150degC, VDSS =max	1000 hrs	Pass	0/22	Temp Humidity Storage	Ta=85degC, RH=85%	1000 hrs	Pass	0/22	Temperature Cycle	Ta=-55degC to 150degC 30min each	100 cycles	Pass	0/22	Pressure Cooker	Ta=121degC, 2.03x105Pa, 100%	50 hrs	Pass	0/22	High Temperature Storage	Ta=150degC	1000 hrs	Pass	0/22	Resistance to Soldering heat(Reflow)	Solder Temp.: 260degC±5degC	10 s	Pass	0/22	Solderability	Solder Temp.: 245degC±5degC	5 s	Pass	0/22
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Electrical Characteristic Summary: There is no change in the electrical performance. Datasheet specifications remain unchanged.																																																	
List of affected Standard Parts: 2SJ652-1E 2SJ661-1E 2SJ661-DL-1E																																																	